

YJ Planar Schottky Barrier Diode Die Specification

200V 60A, 230mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB230S200AS-290F

Main Products Characterstics

Maximum Ratings

Static Electrical Characteristics (Ta = 25°C)

$I_F = 60A$

$\leq 2\%$

Device Schematics and Outline Drawing

- Die Thickness *
- Die Size **
- Top Metal Pad
- Active Area
- Top Metal
- Back Metal
- Note: 1 * : Also can offer device with 8 mils thickness
- 2 ** : Cutting street width is around 1.5 mils

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.
does not guarantee device performance after assembly.

Recommended Storage Environment:
Store in original container, in dessicated nitrogen, with no contamination.